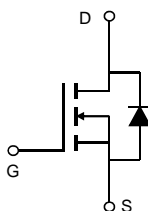


General Description

The AON2400 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

| | |
|------------------------------------|----------------|
| V_{DS} | 8V |
| I_D (at $V_{GS}=4.5V$) | 8A |
| $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) | < 11m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 1.8V$) | < 13m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 1.5V$) | < 16m Ω |
| $R_{DS(ON)}$ (at $V_{GS} = 1.2V$) | < 23m Ω |



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|-------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 8 | V |
| Gate-Source Voltage | V_{GS} | ± 5 | V |
| Continuous Drain Current ^G | I_D | $T_A=25^\circ\text{C}$ | 8 |
| | | $T_A=100^\circ\text{C}$ | 6 |
| Pulsed Drain Current ^C | I_{DM} | 32 | A |
| Power Dissipation ^A | P_D | $T_A=25^\circ\text{C}$ | 2.8 |
| | | $T_A=70^\circ\text{C}$ | 1.8 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|---------------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 37 | 45 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A,D} | | Steady-State | 66 | 80 |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|-----|-----------|----------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 8 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =8V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} =±5V | | | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | | 0.46 | | V |
| I _{D(ON)} | On state drain current | V _{GS} =4.5V, V _{DS} =5V | 32 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =2.5V, I _D =8A T _J =125°C | | 8.5 11 | 11 14 | mΩ |
| | | V _{GS} =1.8V, I _D =6A | | 10 | 13 | |
| | | V _{GS} =1.5V, I _D =5A | | 11.5 | 16 | |
| | | V _{GS} =1.2V, I _D =3A | | 16 | 23 | |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =8A | | 100 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.53 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 4.5 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =4V, f=1MHz | | 1645 | | pF |
| C _{oss} | Output Capacitance | | | 470 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 320 | | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | | 1.6 | 3.2 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g | Total Gate Charge | V _{GS} =4.5V, V _{DS} =4V, I _D =8A | | 16 | | nC |
| Q _{gs} | Gate Source Charge | | | 2 | | nC |
| Q _{gd} | Gate Drain Charge | | | 2.8 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =4.5V, V _{DS} =4V, R _L =0.5Ω, R _{GEN} =3Ω | | 7 | | ns |
| t _r | Turn-On Rise Time | | | 25 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 37 | | ns |
| t _f | Turn-Off Fall Time | | | 13 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =8A, dI/dt=100A/μs | | 17 | | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =8A, dI/dt=100A/μs | | 9 | | nC |

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

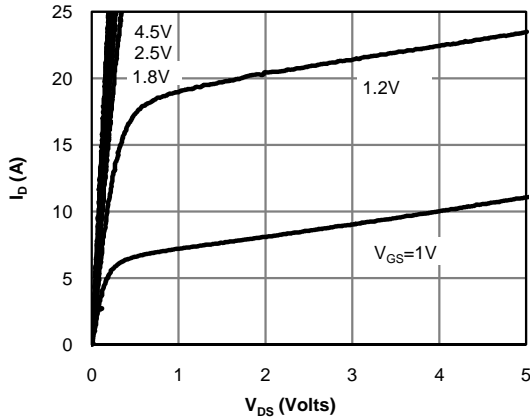


Fig 1: On-Region Characteristics (Note E)

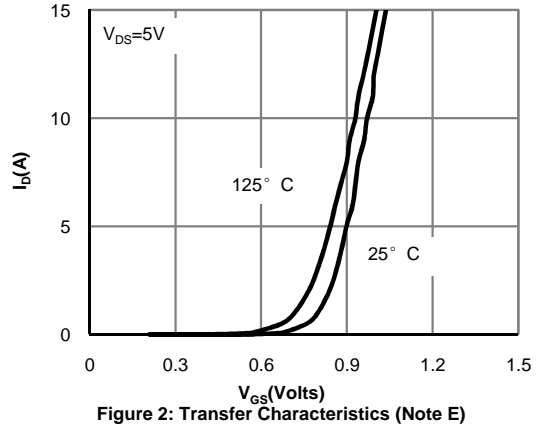


Figure 2: Transfer Characteristics (Note E)

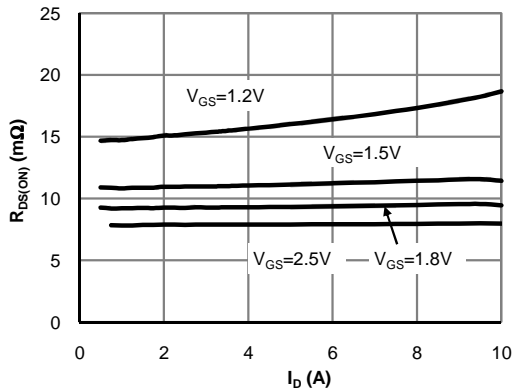


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

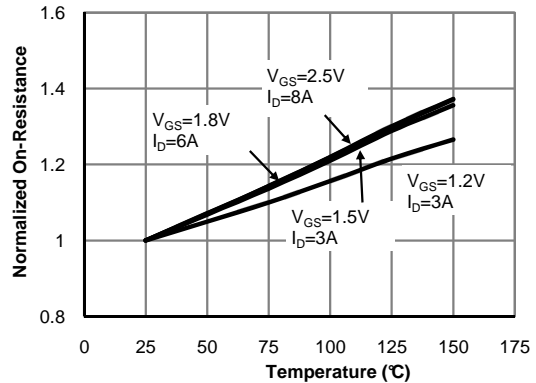


Figure 4: On-Resistance vs. Junction Temperature (Note E)

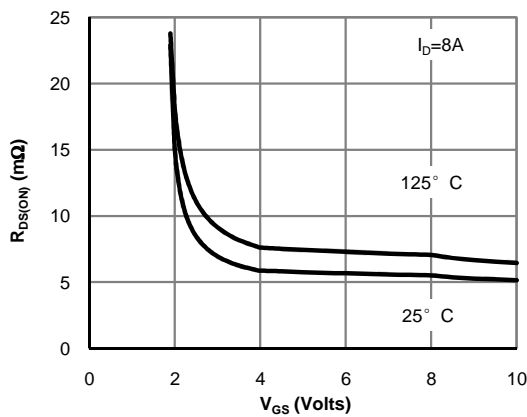


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

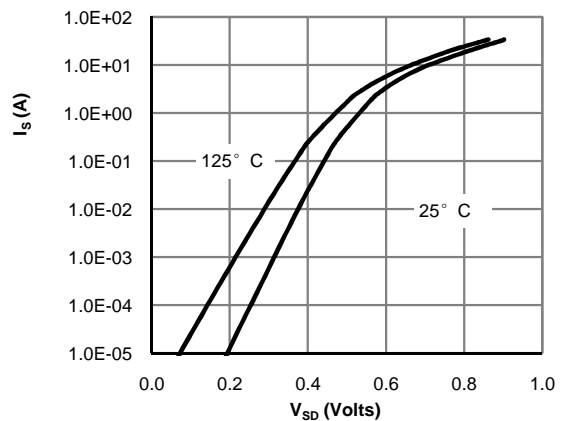


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

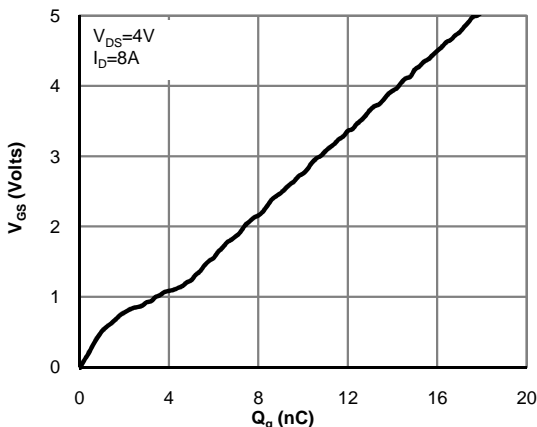


Figure 7: Gate-Charge Characteristics

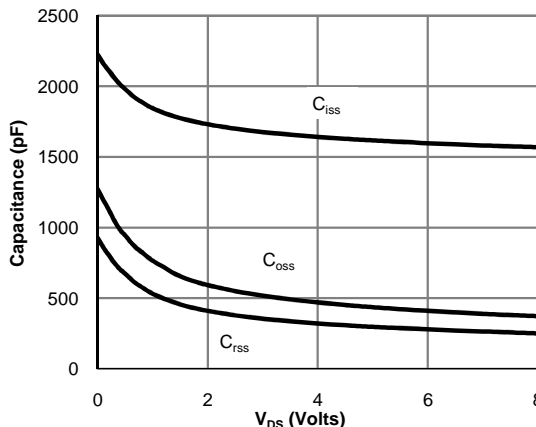


Figure 8: Capacitance Characteristics

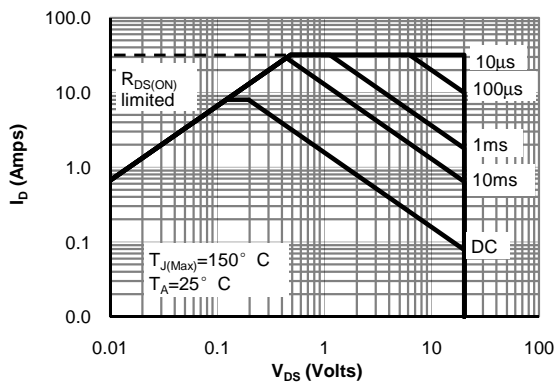


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

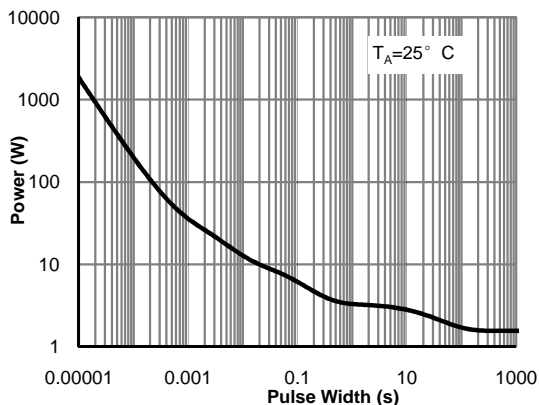


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note H)

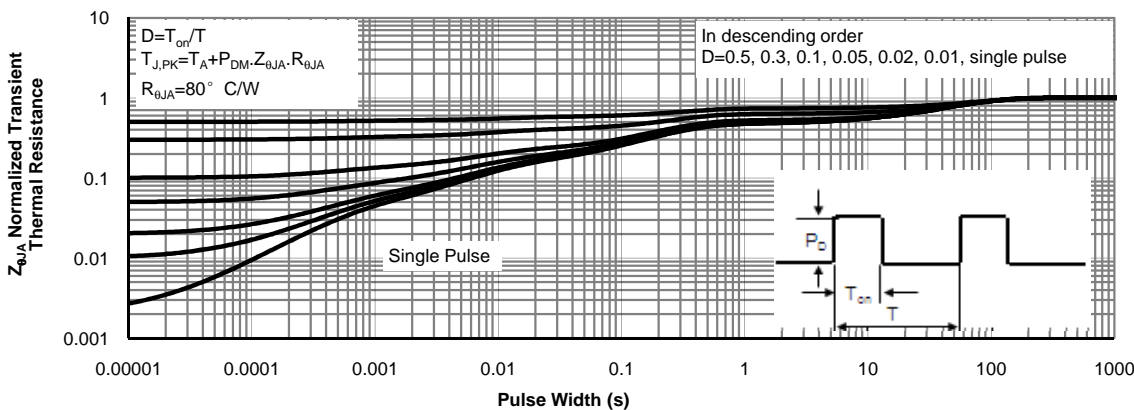
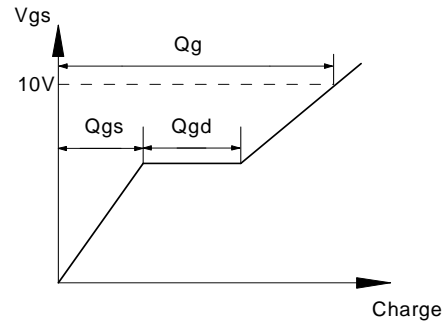
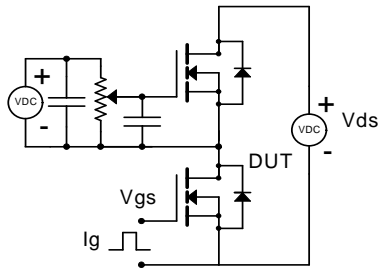
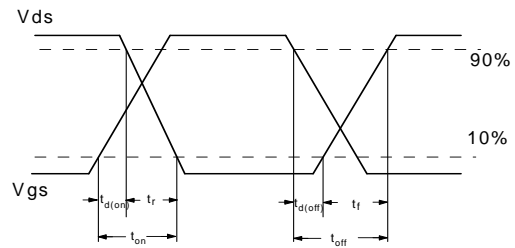
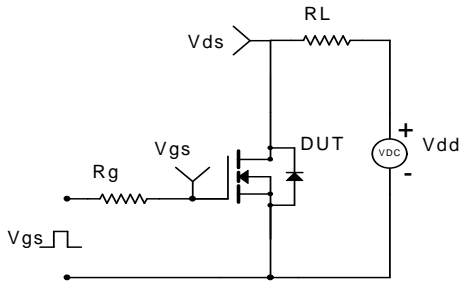


Figure 12: Normalized Maximum Transient Thermal Impedance (Note H)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

